

AMENDMENTS TO THE SPECIFICATION

Kindly replace paragraph [0036] with the following amended paragraph:

[0036] At this time, the controlling section 160 measures the degree of vacuum in the vacuum chamber 10 through a sensor ~~senor~~ (not shown) for detecting the degree of vacuum (hereinafter, referred to as a vacuum degree detection sensor). If it is determined that an excessive amount of gas is injected into the vacuum chamber 10, the controlling section 160 activates the gas discharging section 150 so that the gas injected into the vacuum chamber is appropriately discharged from the vacuum chamber 10. Subsequently, when the vacuum chamber 10 reaches a stable state at a preset degree of vacuum, in step S340, the controlling section 160 activates the bonding section 140 to bond the semiconductor substrate 30 and the cover 20. This bonding is performed similar to an existing anodic bonding process. More particularly, during the bonding operation, a predetermined amount of heat is applied to the cover 20, which may be a glass plate, and then a high voltage is applied to the cover 20 during the heating at a predetermined, elevated temperature. In an embodiment of the present invention, a predetermined amount of time may be allowed to elapse after injecting the inert gas and prior to bonding the semiconductor substrate 30 and the cover 20. The predetermined time refers to a time when the degree of vacuum in the vacuum chamber has stabilized.